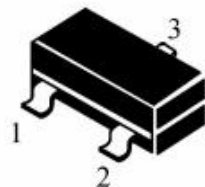
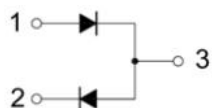


Switching Diode 开关二极管

■SOT-23 Internal Configuration 内部结构



■Features 特点

Characteristic 特性参数	Symbol 符号	Max 最大值	Unit 单位
Power dissipation 耗散功率	$P_D(T_a=25^{\circ}\text{C})$	225	mW
Forward Current 正向电流	I_F	150	mA
Non-Repetitive Peak Forward Current 不重复峰值正向电流	I_{FM}	300	mA
Non-Repetitive Peak Surge Current@ $t=1\mu\text{s}$ 不重复峰值浪涌电流@ $t=1\text{s}$	I_{FSM}	$\begin{matrix} 2 \\ 1 \end{matrix}$	A
Reverse Voltage 反向电压	V_R	100	V
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	556	$^{\circ}\text{C}/\text{W}$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	-55to+150 $^{\circ}\text{C}$	

■Device Marking 产品打标

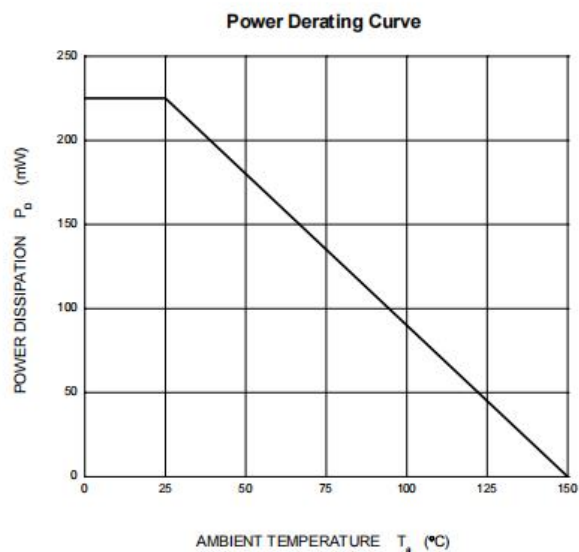
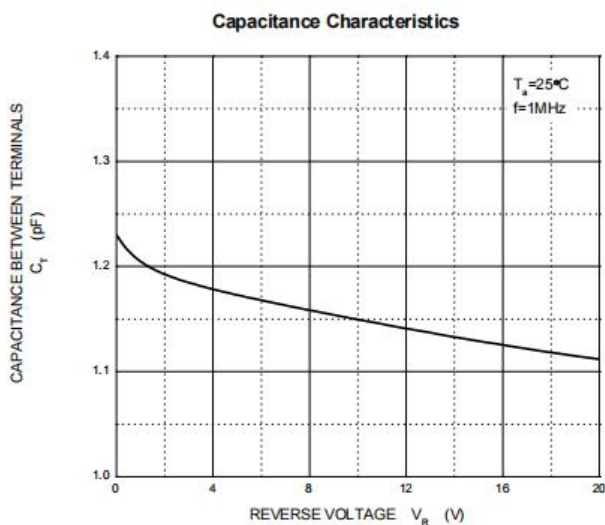
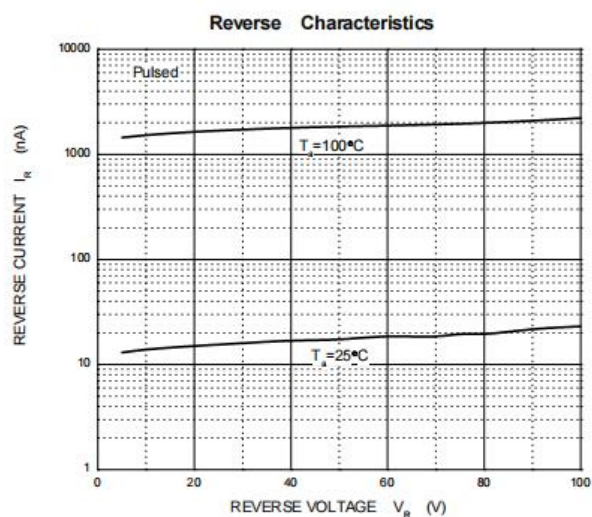
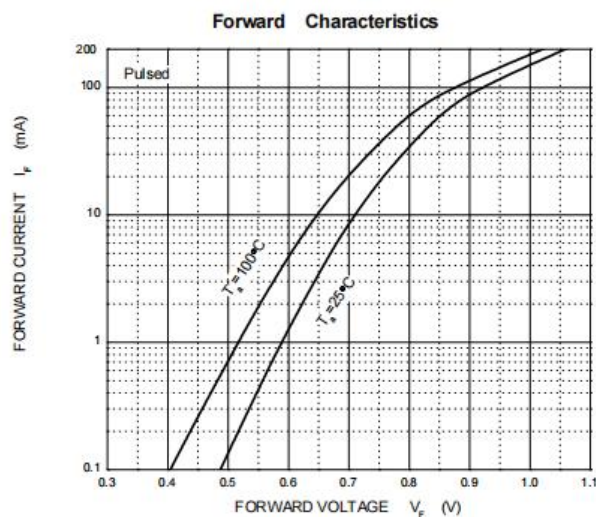
MMBD7000=M5C

■Electrical Characteristics 电特性

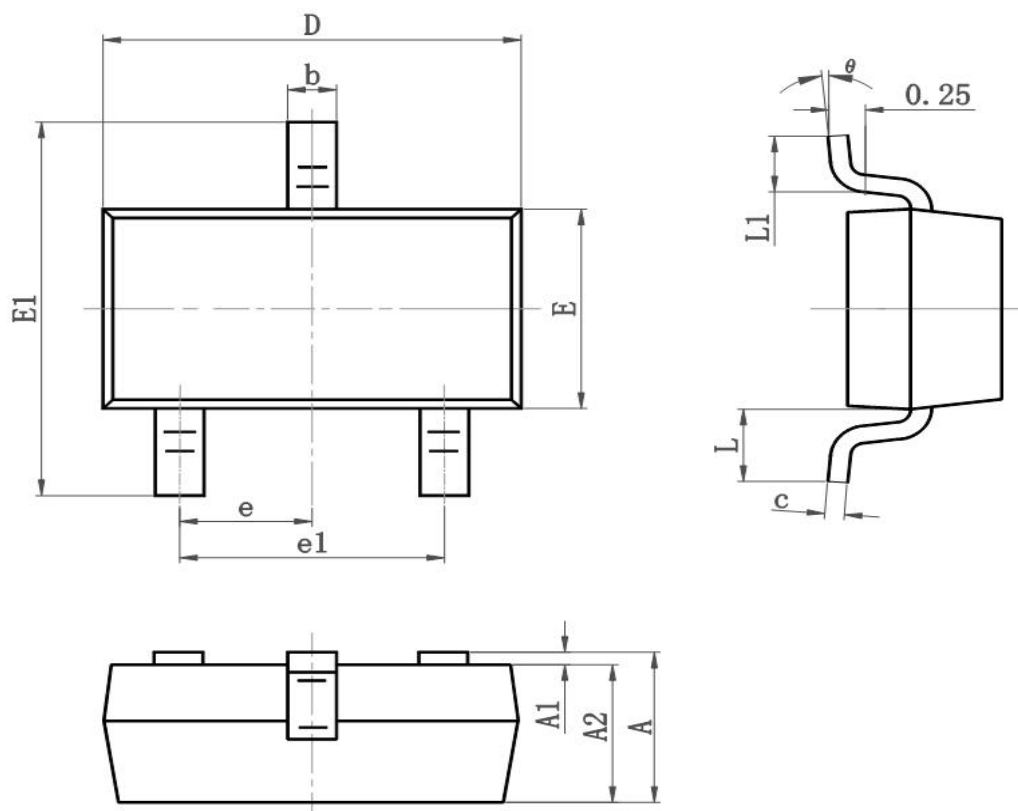
(TA=25 $^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25 $^{\circ}\text{C}$)

Characteristic 特性参数	Symbol 符号	Min 最小值	Max 最大值	Unit 单位
Reverse Breakdown Voltage 反向击穿电压 ($I_R=100\mu\text{A}$)	$V_{(BR)}$	100	—	V
Reverse Leakage Current($V_R=50\text{V}$) 反向漏电流($V_R=100\text{V}$)	I_R	—	$\begin{matrix} 1 \\ 3 \end{matrix}$	$\begin{matrix} \mu\text{A} \\ \mu\text{A} \end{matrix}$
Forward Voltage($I_F=1\text{mA}$) 正向电压($I_F=10\text{mA}$) ($I_F=100\text{mA}$) ($I_F=150\text{mA}$)	V_F	$\begin{matrix} 0.55 \\ 0.67 \\ 0.75 \end{matrix}$	$\begin{matrix} 0.7 \\ 0.82 \\ 1.10 \\ 1.25 \end{matrix}$	V
Diode Capacitance 二极管电容 ($V_R=0\text{V}$, $f=1\text{MHz}$)	C_D	—	2	pF
Reverse Recovery Time 反向恢复时间	T_{rr}	—	4	nS

■ Typical Characteristic Curve 典型特性曲线



■Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.050	0.055
E1	2.250	2.550	0.089	0.100
e	0.900	1.00	0.035	0.039
e1	1.800	2.000	0.071	0.079
L	0.500	0.600	0.020	0.024
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°